

KM48C514B, KM48V514B**CMOS DRAM****512K x 8 Bit CMOS Dynamic RAM with Extended Data Out****DESCRIPTION**

This is a family of 524,288 x 8 bit Extended Data Out CMOS DRAMs. Extended Data Out offers high speed random access of memory cells within the same row. Power supply voltage (+5.0V or +3.3V), access time (-5, -6, -7 or -8), power consumption (Normal or Low power) and package type (SOJ or TSOP-II) are optional features of this family.

All of this family have $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh, $\overline{\text{RAS}}$ -only refresh and Hidden refresh capabilities. Furthermore, Self-refresh operation is available in Low power version.

This 512Kx8 Extended Data Out DRAM family is fabricated using Samsung's advanced CMOS process to realize high band-width, low power consumption and high reliability.

It may be used as main memory unit for personal computer and portable machines.

FEATURES

• Part Identification

- KM48C514B/BL (5V, 1K Ref.)
- KM48V514B/BL (3.3V, 1K Ref.)

• Active power dissipation

Unit : mW

Speed	3.3V (1K Ref.)	5V (1K Ref.)
-5	-	470
-6	255	385
-7	235	360
-8	220	-

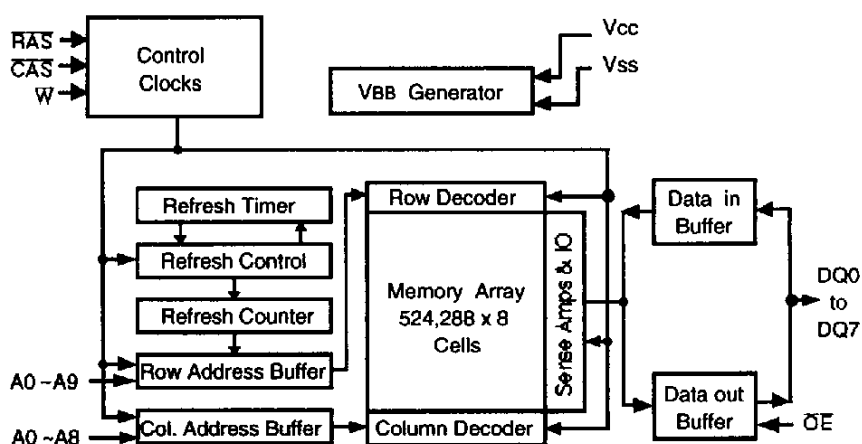
• Refresh cycles

Part NO.	Vcc	Refresh cycle	Refresh Period	
			Normal	L
C514B	5V	1K	16ms	128ms
V514B	3.3V			

• Performance range

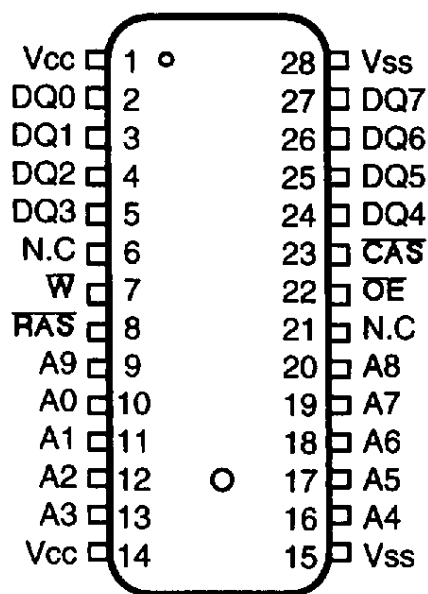
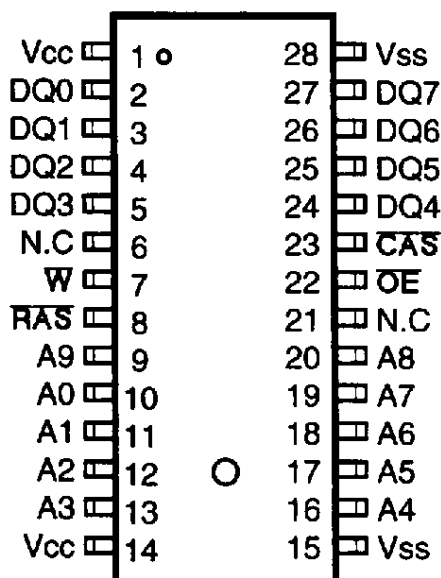
Speed	tRAC	tCAC	tRC	tHPC	Remark
-5	50ns	15ns	84ns	20ns	5V Only
-6	60ns	15ns	104ns	25ns	5V/3.3V
-7	70ns	20ns	124ns	30ns	5V/3.3V
-8	80ns	20ns	144ns	35ns	3.3V Only

- Extended Data Out operation
- Byte Read/Write operation
- $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh capability
- $\overline{\text{RAS}}$ -only and Hidden refresh capability
- Self-refresh capability (L-ver only)
- TTL(5V)/LVTTTL(3.3V) compatible inputs and outputs
- Early Write or output enable controlled write
- JEDEC standard pinout
- Available in plastic SOJ and TSOP(II) packages
- Dual +5V $\pm$ 10% power supply (5V product)
- Dual +3.3V $\pm$ 0.3V power supply (3.3V product)

FUNCTIONAL BLOCK DIAGRAM

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PIN CONFIGURATION (Top Views)**• KM48C/V514BJ****(SOJ)****• KM48C/V514BT****(TSOP(II)-Forward Type)**

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Pin Name	Pin Function	Pin Name	Pin Function
A0 - A9	Address Inputs	W	Read/Write Input
DQ0 -7	Data In/Out	OE	Data Output Enable
Vss	Ground	Vcc	Power (+5V)
RAS	Row Address Strobe	Vcc	Power (+3.3V)
CAS	Column Address Strobe	N.C	No Connection

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating		Units
		3.3V	5V	
Voltage on any pin relative to V _{SS}	V _{IN} , V _{OUT}	-0.5 to +4.6	-1.0 to +7.0	V
Voltage on V _{CC} supply relative to V _{SS}	V _{CC}	-0.5 to +4.6	-1.0 to +7.0	V
Storage Temperature	T _{stg}	-55 to +150	-55 to +150	°C
Power Dissipation	P _D	1	1	W
Short Circuit Output Current	I _{OS}	50	50	mA

* Permanent device damage may occur if "ABSOLUTE MAXIMUM RATINGS" are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS (Voltages referenced to V_{SS}, T_A = 0 to 70 °C)

Parameter	Symbol	3.3V			5V			Unit
		Min	Typ	Max	Min	Typ	Max	
Supply Voltage	V _{CC}	3.0	3.3	3.6	4.5	5.0	5.5	V
Ground	V _{SS}	0	0	0	0	0	0	V
Input High Voltage	V _{IH}	2.1	-	V _{CC} +0.3 ^{*1}	2.4	-	V _{CC} +1.0 ^{*1}	V
Input Low Voltage	V _{IL}	-0.3 ^{*2}	-	0.8	-1.0 ^{*2}	-	0.8	V

*1 : V_{CC}+1.3V/15ns(3.3V), V_{CC}+2.0V/20ns(5V), Pulse width is measured at V_{CC}.

*2 : -1.3V/15ns(3.3V), -2.0V/20ns(5V), Pulse width is measured at V_{SS}.

DC AND OPERATING CHARACTERISTICS

(Recommended operating conditions unless otherwise noted.)

	Parameter	Symbol	Min	Max	Units
3.3V	Input Leakage Current (Any input 0 ≤ V _{IN} ≤ V _{CC} +0.3V, all other pins not under test=0V)	I _{I(L)}	-5	5	μA
	Output Leakage Current (Data out is disabled, 0V ≤ V _{OUT} ≤ V _{CC})	I _{O(L)}	-5	5	μA
	Output High Voltage Level (I _{OH} =-2mA)	V _{OH}	2.4	-	V
	Output Low Voltage Level (I _{OL} =2mA)	V _{OL}	-	0.4	V
5V	Input Leakage Current (Any input 0 ≤ V _{IN} ≤ V _{CC} +0.5V, (Any input 0 ≤ V _{IN} ≤ V _{CC} +0.5V, all other pins not under test=0V)	I _{I(L)}	-5	5	μA
	Output Leakage Current (Data out is disabled, 0V ≤ V _{OUT} ≤ V _{CC})	I _{O(L)}	-5	5	μA
	Output High Voltage Level (I _{OH} =-5mA)	V _{OH}	2.4	-	V
	Output Low Voltage Level (I _{OL} =4.2mA)	V _{OL}	-	0.4	V

DC AND OPERATING CHARACTERISTICS

(Recommended operating conditions unless otherwise noted.)

Symbol	Power	Speed	Max		Units
			KM48V514B	KM48C514B	
Icc1	Don't care	-5	-	85	mA
		-6	70	70	mA
		-7	65	65	mA
		-8	60	-	mA
Icc2	Don't care	Don't care	1	2	mA
Icc3	Don't care	-5	-	85	mA
		-6	70	70	mA
		-7	65	65	mA
		-8	60	-	mA
Icc4	Don't care	-5	-	65	mA
		-6	55	55	mA
		-7	50	50	mA
		-8	45	-	mA
Icc5	Normal L	Don't care	0.5	1	mA
			100	150	μA
Icc6	Don't care	-5	-	85	mA
		-6	70	70	mA
		-7	65	65	mA
		-8	60	-	mA
Icc7	L	Don't care	200	300	μA
Icc8	L	Don't care	100	200	μA

Icc1* : Operating current ($\overline{RAS}$, $\overline{CAS}$, Address cycling @tRC=min.)Icc2 : Standby current ($\overline{RAS}=\overline{CAS}=W=V_{IH}$)Icc3* : $\overline{RAS}$ -only refresh current ($\overline{CAS}=V_{IH}$, $\overline{RAS}$, Address cycling @tRC=min.)Icc4* : Hyper Page Mode current ($\overline{RAS}=V_{IL}$, $\overline{CAS}$, Address cycling @tHPC=min.)Icc5 : Standby current ($\overline{RAS}=\overline{CAS}=W=V_{CC}-0.2V$)Icc6* : $\overline{CAS}$ -before- $\overline{RAS}$ Refresh current ($\overline{RAS}$ and $\overline{CAS}$ cycling @tRC=min.)

Icc7 : Battery back-up current, Average power supply current, Battery back-up mode

Input high voltage(V_{IH})= $V_{CC}-0.2V$, Input low voltage(V_{IL})= $0.2V$, $\overline{CAS}=0.2V$

Din = Don't care, tRC=125μs, tRAS=tRAS min~300 ns

Icc8 : Self refresh current

 $\overline{RAS}=\overline{CAS}=V_{IL}$, $W=\overline{OE}=A0 \sim A9 = V_{CC}-0.2V$ or $0.2V$,DQ0 ~ DQ7 = $V_{CC}-0.2V$, $0.2V$ or open

* NOTE : Icc1, Icc3, Icc4 and Icc6 are dependent on output loading and cycle rates. Specified values are obtained with the output open. Icc is specified as an average current. In Icc1, Icc3, and Icc6, address can be changed maximum once while $\overline{RAS}=V_{IL}$. In Icc4, address can be changed maximum once within one hyper page cycle time, tHPC

CAPACITANCE ($T_A=25^{\circ}\text{C}$, $V_{CC}=5\text{V}$ or 3.3V , $f=1\text{MHz}$)

Parameter	Symbol	Min	Max	Unit
Input capacitance [A0 ~ A9]	C_{IN1}	-	5	pF
Input capacitance [$\overline{\text{RAS}}$, $\overline{\text{CAS}}$, W, $\overline{\text{OE}}$]	C_{IN2}	-	7	pF
Output Capacitance [DQ0 ~ DQ7]	C_{DQ}	-	7	pF

AC CHARACTERISTICS ($0^{\circ}\text{C} \leq T_A \leq 70^{\circ}\text{C}$, See note 1,2)Test condition (5V device) : $V_{CC}=5.0\text{V} \pm 10\%$, $V_{IH}/V_{IL}=2.4/0.8\text{V}$, $V_{OH}/V_{OL}=2.0/0.8\text{V}$ Test condition (3.3V device) : $V_{CC}=3.3\text{V} \pm 0.3\text{V}$, $V_{IH}/V_{IL}=2.1/0.8\text{V}$, $V_{OH}/V_{OL}=2.0/0.8\text{V}$

Parameter	Symbol	- 5*1		- 6		- 7		- 8*2		Units	Notes
		Min	Max	Min	Max	Min	Max	Min	Max		
Random read or write cycle time	tRC	84		104		124		144		ns	
Read-modify-write cycle time	tRWC	116		140		165		190		ns	
Access time from $\overline{\text{RAS}}$	tRAC		50		60		70		80	ns	3,4,10
Access time from $\overline{\text{CAS}}$	tCAC		17		17		20		20	ns	3,4,5
Access time from column address	tAA		25		30		35		40	ns	3,10
$\overline{\text{CAS}}$ to output in Low-Z	tCLZ	3		3		3		3		ns	3
Output buffer turn-off delay from $\overline{\text{CAS}}$	tCEZ	3	13	3	15	3	15	3	15	ns	6, 13
Transition time (rise and fall)	tT	2	50	2	50	2	50	2	50	ns	2
$\overline{\text{RAS}}$ precharge time	tRP	30		40		50		60		ns	
$\overline{\text{RAS}}$ pulse width	tRAS	50	10K	60	10K	70	10K	80	10K	ns	
$\overline{\text{RAS}}$ hold time	tRSH	17		17		20		20		ns	
$\overline{\text{CAS}}$ hold time	tCSH	40		50		60		70		ns	
$\overline{\text{CAS}}$ pulse width	tCAS	8	10K	10	10K	15	10K	20	10K	ns	11
$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ delay time	tRCD	20	33	20	43	20	50	20	60	ns	4
$\overline{\text{RAS}}$ to column address delay time	tRAD	15	25	15	30	15	35	15	40	ns	10
$\overline{\text{CAS}}$ to $\overline{\text{RAS}}$ precharge time	tCRP	5		5		5		5		ns	
Row address set-up time	tASR	0		0		0		0		ns	
Row address hold time	tRAH	10		10		10		10		ns	
Column address set-up time	tASC	0		0		0		0		ns	
Column address hold time (5V)	tCAH	8		10		15		-		ns	
Column address hold time (3.3V)	tCAH	-		15		15		15		ns	
Column address to $\overline{\text{RAS}}$ lead time	tRAL	25		30		35		40		ns	
Read command set-up time	tRCS	0		0		0		0		ns	
Read command hold time referenced to $\overline{\text{CAS}}$	tRCH	0		0		0		0		ns	8
Read command hold time referenced to $\overline{\text{RAS}}$	tRRH	0		0		0		0		ns	8
Write command set-up time	tWCS	0		0		0		0		ns	7
Write command hold time	tWCH	10		10		10		10		ns	
Write command pulse width	tWP	10		10		10		10		ns	
Write command to $\overline{\text{RAS}}$ lead time	tRWL	13		15		15		20		ns	
Write command to $\overline{\text{CAS}}$ lead time	tCWL	8		10		15		20		ns	

Note) *1: 50ns product : $V_{CC}=5\text{V} \pm 5\%$, Output Loading(C_L)=50pF, *2 : 3.3V only

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AC CHARACTERISTICS (0°C ≤ T_A ≤ 70°C, See note 1,2)

Parameter	Symbol	- 5 ^{*1}		- 6		- 7		- 8 ^{*2}		Units	Notes
		Min	Max	Min	Max	Min	Max	Min	Max		
Data set-up time	t _{DS}	0		0		0		0		ns	9
Data hold time (5V)	t _{DH}	8		10		15		-		ns	9
Data hold time (3.3V)	t _{DH}	-		15		15		15		ns	
Refresh period (Normal)	t _{REF}		16		16		16		16	ms	
Refresh period (L-ver)	t _{REF}		128		128		128		128	ms	
CAS to W delay time	t _{CWD}	34		36		44		44		ns	7
RAS to W delay time	t _{RWD}	67		79		94		104		ns	7
Column address to W delay time	t _{AWD}	42		49		59		64		ns	7
CAS precharge to W delay time	t _{CPWD}	45		54		64		69		ns	
CAS set-up time (CAS-before-RAS refresh)	t _{CSR}	5		5		5		5		ns	
CAS hold time (CAS-before-RAS refresh)	t _{CHR}	10		10		10		10		ns	
RAS to CAS precharge time	t _{RPC}	5		5		5		5		ns	
CAS precharge time (CBR counter test cycle)	t _{CPT}	20		20		25		30		ns	
Access time from CAS precharge	t _{CPA}		28		35		40		45	ns	3
Hyper Page mode cycle time	t _{HPC}	20		25		30		35		ns	11
Hyper Page mode read-modify-write cycle time	t _{HPRWC}	47		56		71		81		ns	11
CAS precharge time (Hyper page cycle)	t _{CP}	8		10		10		10		ns	
RAS pulse width (Hyper page cycle)	t _{RASP}	50	100K	60	100K	70	100K	80	100K	ns	
RAS hold time from CAS precharge	t _{RHCP}	30		35		40		45		ns	
OE access time	t _{OEa}		15		15		20		20	ns	3
OE to data delay	t _{OED}	13		15		20		20		ns	
Output buffer turn off delay time from OE	t _{OEZ}	3	13	3	15	3	20	3	20	ns	6
OE to output in low-Z	t _{OLZ}	3		3		3		3		ns	
OE command hold time	t _{OEh}	13		15		20		20		ns	
Output data hold time	t _{DOH}	5		5		5		5		ns	
Output buffer turn off delay from RAS	t _{REZ}	3	13	3	15	3	20	3	20	ns	6, 13
Output buffer turn off delay from W	t _{WEZ}	3	13	3	15	3	20	3	20	ns	6
W to data delay	t _{WED}	13		15		20		20		ns	
OE to CAS hold time	t _{OECH}	5		5		5		5		ns	
CAS hold time to OE	t _{CHO}	5		5		5		5		ns	
OE precharge time	t _{OEP}	5		5		5		5		ns	
W pulse width (hyper page cycle)	t _{WPE}	5		5		5		5		ns	
RAS pulse width (C-B-R self refresh)	t _{RASS}	100		100		100		100		μs	12
RAS precharge time (C-B-R self refresh)	t _{RPS}	90		110		130		150		ns	12
CAS hold time (C-B-R self refresh)	t _{CHS}	-50		-50		-50		-50		ns	12

Note) *1: 50ns product : V_{CC}=5V±5%, Output Loading(C_L)=50pF, *2: 3.3V only

NOTES

1. An initial pause of 200 μ s is required after power-up followed by any 8 ROR or CBR cycles before proper device operation is achieved.
2. $V_{IH}(\text{min})$ and $V_{IL}(\text{max})$ are reference levels for measuring timing of input signals. Transition times are measured between $V_{IH}(\text{min})$ and $V_{IL}(\text{max})$ and are assumed to be 2ns for all inputs.
3. Measured with a load equivalent to 2 TTL(5V)/1 TTL(3.3V) loads and 100pF.
4. Operation within the $t_{RCD}(\text{max})$ limit insures that $t_{RAC}(\text{max})$ can be met. $t_{RCD}(\text{max})$ is specified as a reference point only. If t_{RCD} is greater than the specified $t_{RCD}(\text{max})$ limit, then access time is controlled exclusively by t_{CAC} .
5. Assumes that $t_{RCD} \geq t_{RCD}(\text{max})$.
6. This parameter defines the time at which the output achieves the open circuit condition and is not referenced to V_{OH} or V_{OL} .
7. t_{WCS} , t_{RWD} , t_{CWD} and t_{AWD} are non restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} \geq t_{WCS}(\text{min})$, the cycles is an early write cycle and the data output will remain high impedance for the duration of the cycle. If $t_{CWD} \geq t_{CWD}(\text{min})$, $t_{RWD} \geq t_{RWD}(\text{min})$ and $t_{AWD} \geq t_{AWD}(\text{min})$, then the cycle is a read-modify-write cycle and the data output will contain the data read from the selected address. If neither of the above conditions is satisfied, the condition of the data out is indeterminate.
8. Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
9. These parameters are referenced to the $\overline{\text{CAS}}$ leading edge in early write cycles and to the $\overline{\text{W}}$ leading edge in read-modify-write cycles.
10. Operation within the $t_{RAD}(\text{max})$ limit insures that $t_{RAC}(\text{max})$ can be met. $t_{RAD}(\text{max})$ is specified as a reference point only. If t_{RAD} is greater than the specified $t_{RAD}(\text{max})$ limit, then access time is controlled by t_{AA} .
11. $t_{ASC} \geq 6\text{ns}$, Assume $t_T = 2.0\text{ns}$.
12. For all of the refresh modes except for distributed $\overline{\text{CAS}}$ -Before- $\overline{\text{RAS}}$ refresh, 1024 cycle of burst refresh must be executed within 8ms before and after self refresh in order to meet refresh specification (L-version).
13. If $\overline{\text{RAS}}$ goes high before $\overline{\text{CAS}}$ high going, the open circuit condition of the output is achieved by $\overline{\text{CAS}}$ high going. If $\overline{\text{CAS}}$ goes high before $\overline{\text{RAS}}$ high going, the open circuit condition of the output is achieved by $\overline{\text{RAS}}$ high going.